# NSN 5962-01-408-0767

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# **Maximum Power Dissipation Rating:**

330.0 milliwatts

# **Operating Tempurature Range:**

-55.0/+125.0 degrees celsius

# **Storage Tempurature Range:**

-65.0/+150.0 degrees celsius

# **End Application:**

Milstar

#### **Features Provided:**

Burn in, mil-std-883, class b and electrostatic sensitive and monolithic and programmed and radiation hardened and tested to mil-std-883 and ultraviolet erasable and w/enable

# **Inclosure Material:**

Ceramic

#### **Inclosure Configuration:**

Dual-in-line

# **Output Logic Form:**

Complementary-metal oxide-semiconductor logic

# **Input Circuit Pattern:**

27 input

# **Criticality Code Justification:**

Cbbl

# **Current Rating Per Characteristic:**

1.00 milliamperes reverse current, dc blank and 10.00 microamperes reverse current, dc microamperes

# **Terminal Surface Treatment:**

Solder

# **Product Name:**

Microcircuit, digital, memory (hci)

# **Voltage Rating And Type Per Characteristic:**

-0.6 volts power source and 7.0 volts power source

#### **Capitance Rating Per Characteristic:**

12.00 input picofarads and 15.00 output picofarads

# **Time Rating Per Chacteristic:**

200.00 nanoseconds delay

# **Memory Device Type:**

Prom

#### **Special Features:**

Device is a 512k x 8 cmos uveprom; this is an altered item made from rc258-0249-010 which is selected from 258-0249-010 which is a 67268 5962-9175202mxa (27c040); case outline designator cdip2-t32 or gdip1-t32 as designated in mil-std-1835

# **Test Data Document:**

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

#### **Terminal Type And Quantity:**

32 printed circuit

# Shelf Life:

N/a

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In	18	<i>(</i> )+	МЛО	201	ure:

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Demilitarization:

No

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